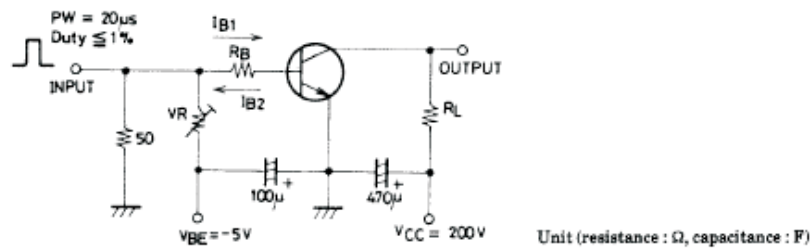


2SC4599

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 500 V, I _E = 0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0			10	μA
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 0.3A	15		50	
		V _{CE} = 5 V, I _C = 1.5A	8			
Gain-Bandwidth product	f _T	V _{CE} = 10 V, I _C = 0.3A		18		MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, f = 1MHz		50		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 1.5 A, I _B = 0.3 A			1.0	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 1.5 A, I _B = 0.3 A			1.5	V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 1 mA, I _E = 0	800			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 5 mA, R _{BE} = ∞	500			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E = 1mA, I _C = 0	7			V
Collector-to-Emitter Sustain Voltage	V _{CEX(SUS)}	I _C = 1.5A, I _{B1} = 0.6A, L = 2mH, I _{B2} = -0.6A	500			V
Turn-ON time	t _{on}	I _C = 2A, I _{B1} = 0.4A, I _{B2} = -0.8A, R _L = 100 Ω, V _{CC} = 200V			0.5	μs
Storage time	t _{stg}				3.0	
Fall time	t _f				0.3	

■ Switching Time Test Circuit



■ hFE Classification

Rank	L	M	N
hFE	15 to 30	20 to 40	30 to 50